

20V N-Channel Enhancement Mode MOSFET

Voltage 20 V Current 8 A

Features

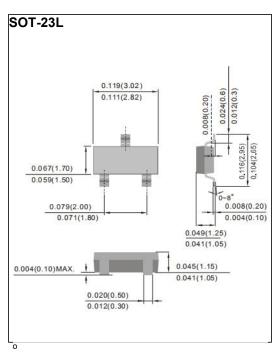
- $R_{DS(ON)}$, $V_{GS}@10V$, $I_D@8A<11m\Omega$
- $R_{DS(ON)}$, $V_{GS}@4.5V$, $I_{D}@6A<15m\Omega$
- Advanced Trench Process Technology
- High density cell design for ultralow on-resistance

Mechanical Data

• Case: S0T23L Package

• Terminals: Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.0004ounces, 0.0085 grams



Maximum Ratings and Thermal Characteristics (TA=25 C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	20	V	
Gate-Source Voltage		V _{GS}	<u>+</u> 12		
Continuous Drain Current	T _C =25°C	I _D	8	А	
	T _C =100°C	ם יו	6		
Pulsed Drain Current(Note 1)	T _C =25°C	I _{DM}	16	1	
Power Dissipation	T _C =25°C	. P _D	1.5	W	
1 OWE DISSIPATION	Derate above 25°C		12		
Operating Junction and Storage Temperature Range		T_{J}, T_{STG}	-55~150	°C	
Typical Thermal Resistance ^(Note 4,5)				- °C/W	
Typical Memai Resistance	Junction to Ambient	$R_{\theta JA}$	80		

• Limited only By Maximum Junction Temperature



Electrical Characteristics (T_A=25 °C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static							
Drain-Source Breakdown Voltage	BV _{DSS} V _{GS} =0V,I _D =250uA		20	-	-	V	
Gate Threshold Voltage	$V_{GS(th)}$	$V_{GS(th)}$ $V_{DS}=V_{GS},I_D=250uA$		1.75	2.5		
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V,I _D =8A	-	8.5	11	mΩ	
		V _{GS} =4.5V,I _D =6A	-	11.5	15		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =20V,V _{GS} =0V	-	-	1.0	uA	
Gate-Source Leakage Current	I_{GSS}	V _{GS} = <u>+</u> 12V,V _{DS} =0V	-	-	<u>+</u> 100	nA	
Dynamic (Note 6)							
Total Gate Charge	Q_g	\/ 00\/ L 40A	-	10	-	nC	
Gate-Source Charge	Q_gs	V_{DS} =20V, I_{D} =10A, V_{GS} =4.5V (Note 2,3)	-	3.5	-		
Gate-Drain Charge	Q_gd	V _{GS} -4.3V	-	3.6	-		
Input Capacitance	Ciss	N/ 00\/ \/ 0\/	-	1040	-	pF	
Output Capacitance	Coss	V _{DS} =20V, V _{GS} =0V, f=1.0MHZ	-	117	-		
Reverse Transfer Capacitance	Crss	I-I.UIVITZ	-	84	-		
Turn-On Delay Time	td _(on)	V _{DS} =20V, I _D =1A,	-	9.4	-		
Turn-On Rise Time	t _r	V_{GS} =10V, R_{G} =6 Ω	-	19	-	ns	
Turn-Off Delay Time	td _(off)	(Note 2,3)	-	66	-		
Turn-Off Fall Time	t _f		-	67	-		
Drain-Source Diode							
Maximum Continuous Drain-Source	I.			42	A		
Diode Forward Current	Is		<u>-</u>	-	42	Α	
Diode Forward Voltage	V_{SD}	I _S =1A,V _{GS} =0V	_	0.7	1	V	

NOTES:

- 1. Pulse width < 300us, Duty cycle < 2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature T_{J(MAX)}=150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. R_{OJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTIC CURVES

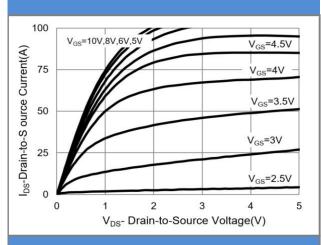


Fig.1 On-Region Characteristics

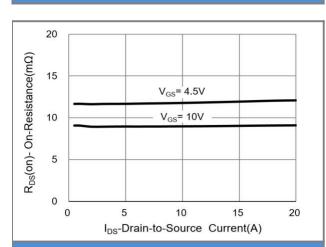


Fig.3 On-Resistance vs. Drain Current

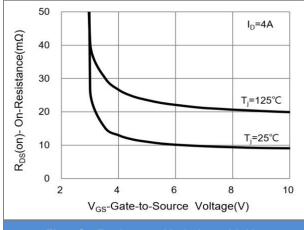


Fig.5 On-Resistance Variation with V_{GS}

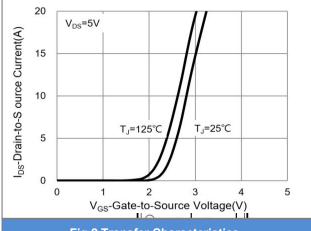


Fig.2 Transfer Characteristics

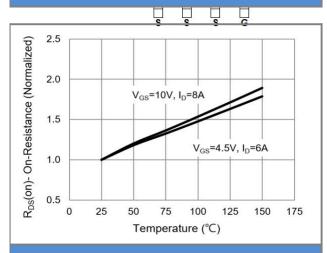


Fig.4 On-Resistance vs. Junction temperature

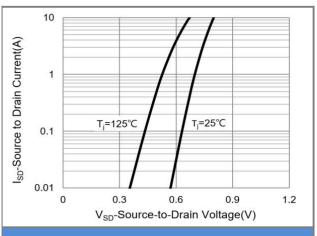


Fig.6 Source-Drain Diode Forward Voltage



TYPICAL CHARACTERISTIC CURVES

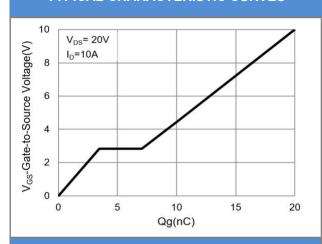


Fig.7 Gate-Charge Characteristics

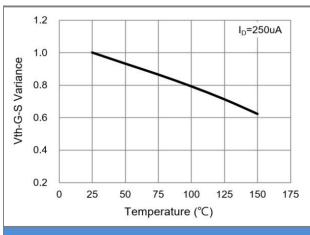


Fig.9 Threshold Voltage Variation with Temperature

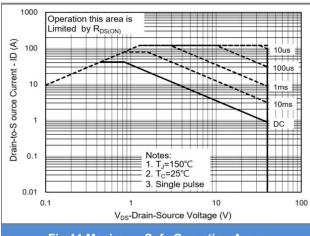


Fig.11 Maximum Safe Operating Area

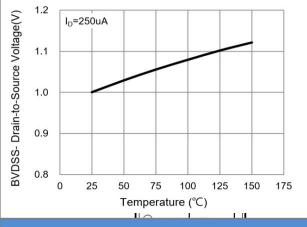


Fig.8 Breakdown Voltage Variation vs. Temperature

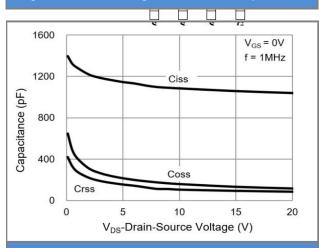


Fig.10 Capacitance vs. Drain-Source Voltage

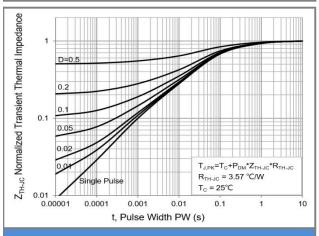


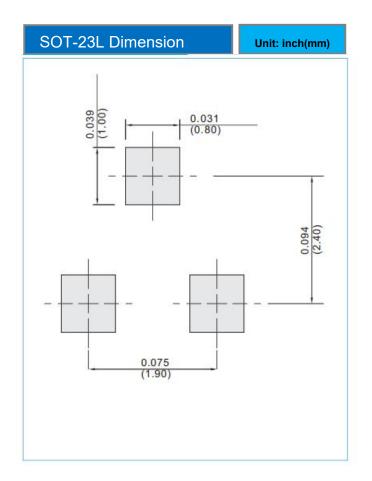
Fig.12 Normalized Transient Thermal Impedance



Part No Packing Code Version

Part No Packing Code	Package Type	Packing Type
CSM212N8S23L	SOT-23L	5K pcs / 13" reel

Packaging Information & Mounting Pad Layout





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